



## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-30V	90mΩ @ V <sub>GS</sub> = -10V	-3.8A
	134mΩ @ V <sub>GS</sub> = -4.5V	-3.1A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Load Switch for Portable Devices

#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram

Top View

- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208e3
- Weight: 0.08 grams (Approximate)

Internal Schematic

Top View

# Ordering Information (Note 4)

	Part Number	Case	Packaging					
	DMG2307L-7	SOT23	3,000/Tape & Reel					
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.							

Drain

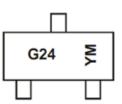
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



 $\begin{array}{l} G24 = \mbox{Product Type Marking Code} \\ \mbox{YM} &= \mbox{Date Code Marking} \\ \mbox{Y or } \overrightarrow{Y} &= \mbox{Year (ex: F = 2018)} \\ \mbox{M} &= \mbox{Month (ex: 9 = September)} \end{array}$ 

Date	Code	Kev
Date	Coue	1100

Year	2018	2019	2020	2021	202	2 20	23 2	024	2025	2026	2027	2028
Code	F	G	Н		J		<	L	М	Ν	0	Р
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) $V_{GS}$ = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-2.5 -2.0	A
Continuous Drain Current (Note 6) $V_{GS}$ = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	Ι <sub>D</sub>	-3.8 -3.0	A
Continuous Drain Current (Note 6) $V_{GS}$ = -10V	t ≦10sec	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-4.6 -3.6	A
Continuous Drain Current (Note 6) $V_{GS}$ = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	Ι <sub>D</sub>	-3.1 -2.5	А
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-20	А	

## **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	Po	0.76	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	159	°C/W
Total Power Dissipation (Note 6)	PD	1.36	W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	94	°C/W
Total Power Dissipation (Note 6) $t \leq 10 \text{sec}$	PD	1.9	W
Thermal Resistance, Junction to Ambient (Note 6) t $\leq$ 10sec	Reja	65.8	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

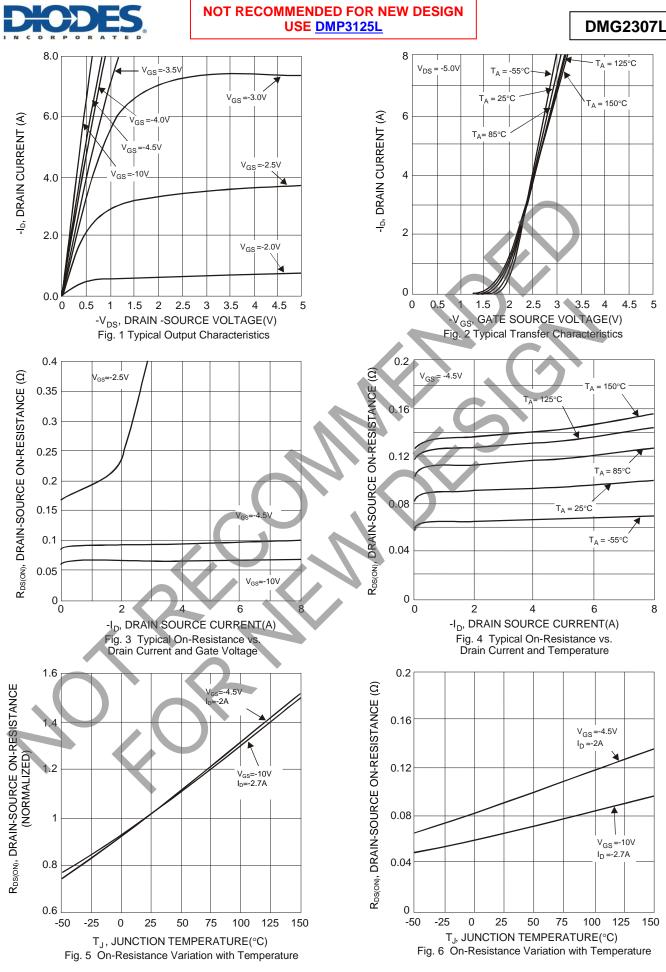
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Symbol	I WILL	тур	IVIAX	Unit	Test condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30			V	$V_{GS} = 0V, I_{D} = -250 \mu A$
Zero Gate Voltage Drain Current $@T_{C} = +25^{\circ}$				-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	Igss	<u> </u>		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)	1 000					
Gate Threshold Voltage	VGS(TH)	-1.0		-3.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance		_	70	90	mΩ	$V_{GS} = -10V, I_D = -2.5A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	105	134	11122	$V_{GS} = -4.5V, I_D = -2.5A$
Forward Transfer Admittance	Y <sub>fs</sub>		4.8		S	$V_{DS} = -10V, I_D = -2.5A$
Diode Forward Voltage (Note 6)	V <sub>SD</sub>		-0.75	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>		371.3		pF	
Output Capacitance	C <sub>oss</sub>	_	51.3	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	—	45.9	_	pF	
Gate Resistance	Rg	_	17		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg		4.0		nC	
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	8.2		nC	$V_{GS} = -10V, V_{DS} = -15V,$
Gate-Source Charge	Qgs		0.9		nC	I <sub>D</sub> = -3A
Gate-Drain Charge	Q <sub>gd</sub>		1.2		nC	
Turn-On Delay Time	t <sub>D(ON)</sub>		4.8		ns	
Turn-On Rise Time	t <sub>R</sub>		7.3	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>		22.4		ns	R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-Off Fall Time	t <sub>F</sub>		13.4		ns	

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.

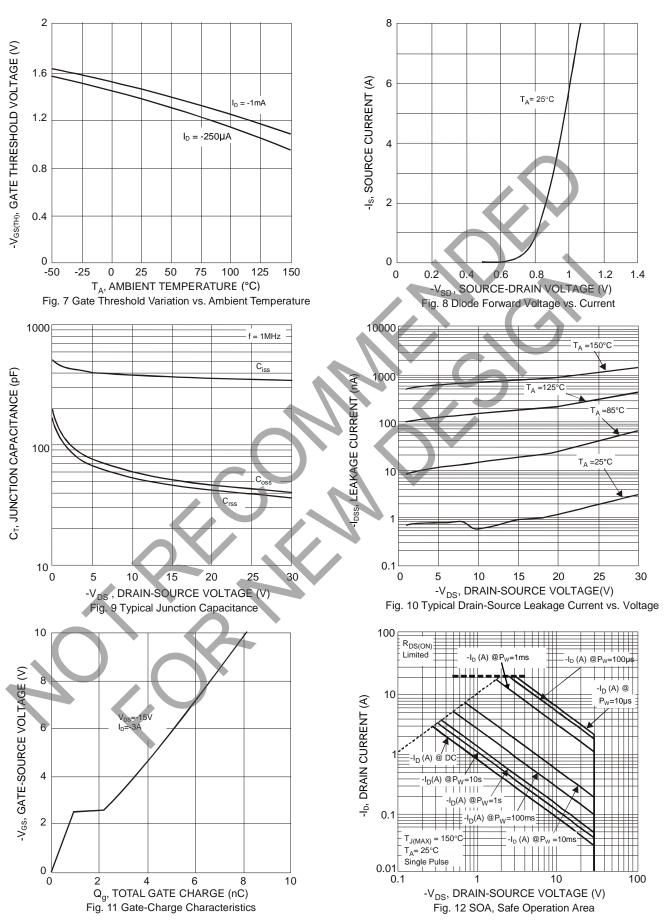
8. Guaranteed by design. Not subject to product testing.





### NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3125L</u>

DMG2307L

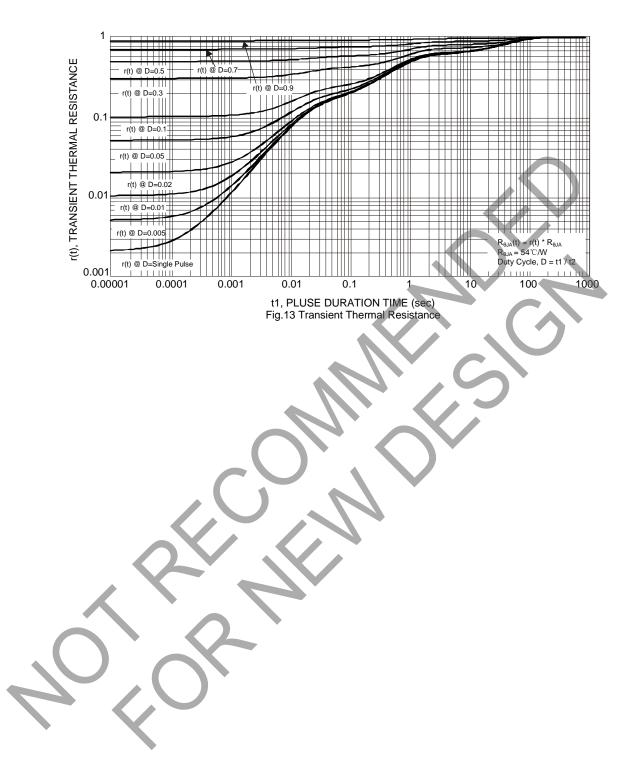


DMG2307L Document number: DS35415 Rev. 5 - 3



### NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3125L</u>

DMG2307L

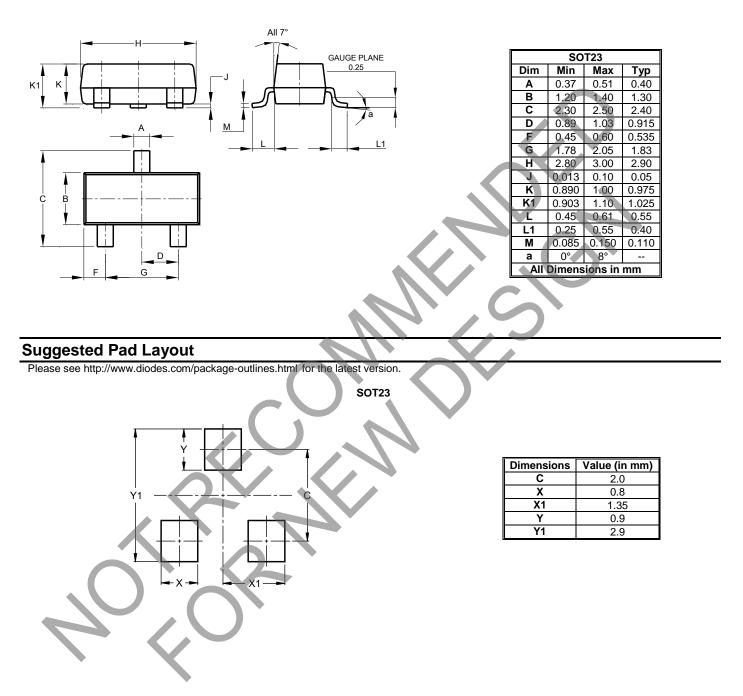




### Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23





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